

**N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**
**Features**

- Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **ESD Protected Up To 2kV**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**

**Mechanical Data**

- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish – Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Terminal Connections: See Diagram
- Weight: 0.002 grams (approximate)

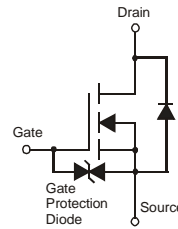


ESD PROTECTED, 2kV

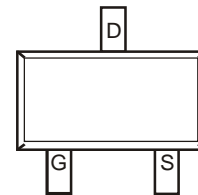


TOP VIEW

SOT523



Equivalent Circuit

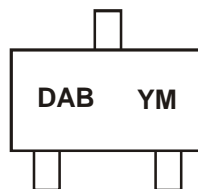


Top View

**Ordering Information** (Note 4)

Part Number	Case	Packaging
DMN5L06TK-7	SOT523	3000/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**


DAB = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: T = 2006)  
 M = Month (ex: 9 = September)

## Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012
Code	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain Source Voltage	V <sub>DSS</sub>	50	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Drain Current (Note 5)	I <sub>D</sub>	280	mA

**Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P <sub>D</sub>	150	mW
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	833	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	50	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	60	nA	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	1	μA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V
				500	nA	V <sub>GS</sub> = ±10V, V <sub>DS</sub> = 0V
				50	nA	V <sub>GS</sub> = ±5V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.49	—	1.2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	1.8	3.0	Ω	V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 50mA
		—	1.5	2.5		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 50mA
		—	1.2	2.0		V <sub>GS</sub> = 5.0V, I <sub>D</sub> = 50mA
On-State Drain Current	I <sub>D(ON)</sub>	0.5	1.4	—	A	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 7.5V
Forward Transconductance	Y <sub>fs</sub>	200	—	—	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.2A
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	0.5	—	1.4	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>	—	—	50	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	—	25	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	—	5.0	pF	

- Notes: 5. Device mounted on FR-4 PCB.  
6. Short duration pulse test used to minimize self-heating effect.

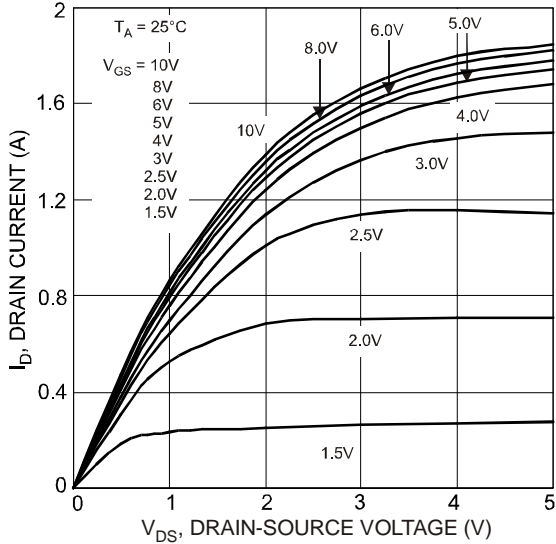


Fig. 1 Typical Output Characteristics

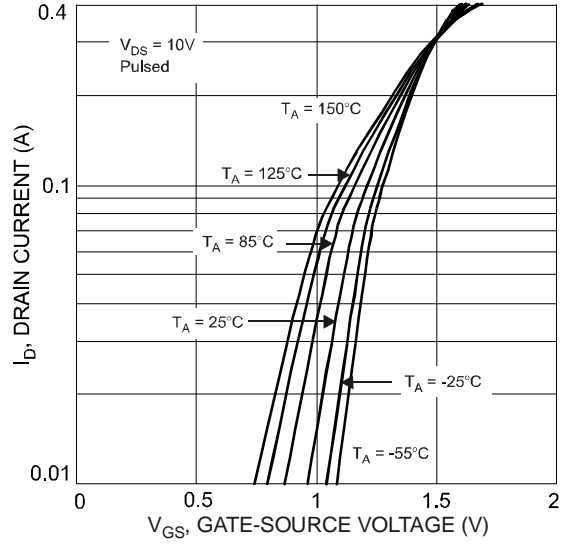


Fig. 2 Typical Transfer Characteristics

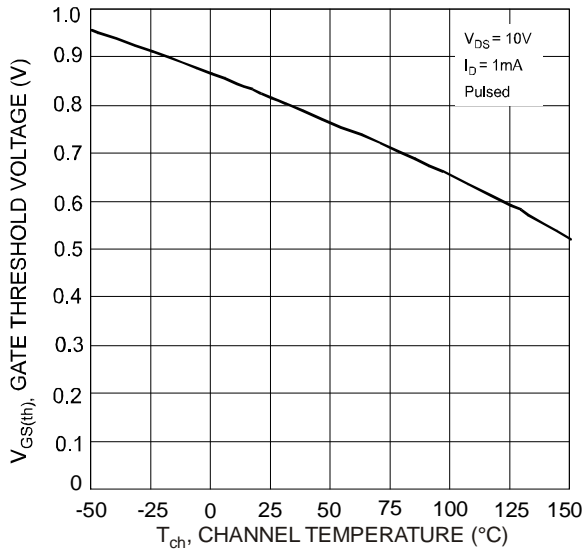


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

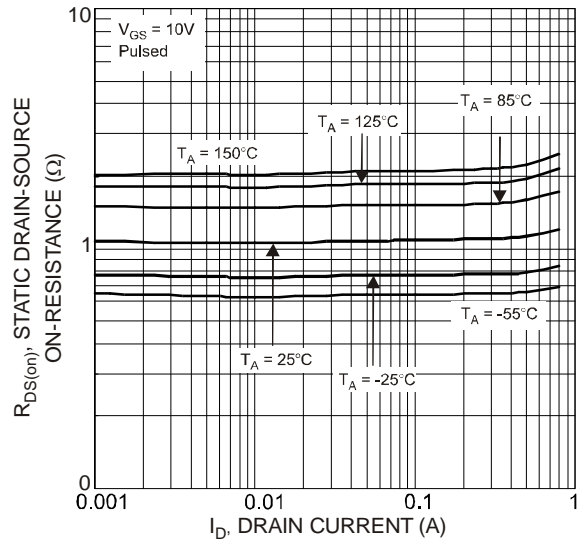


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

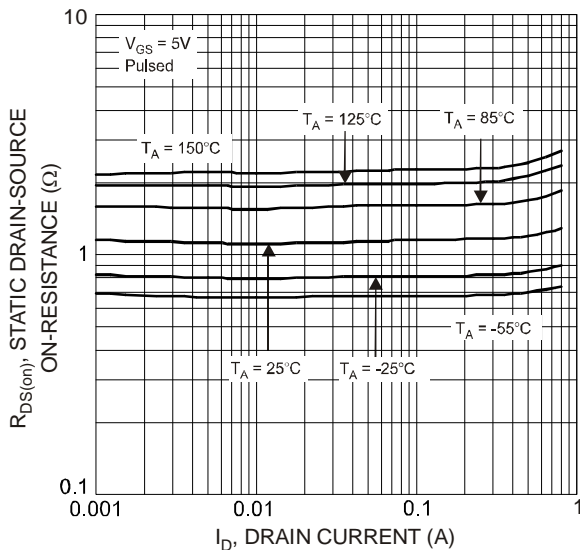


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

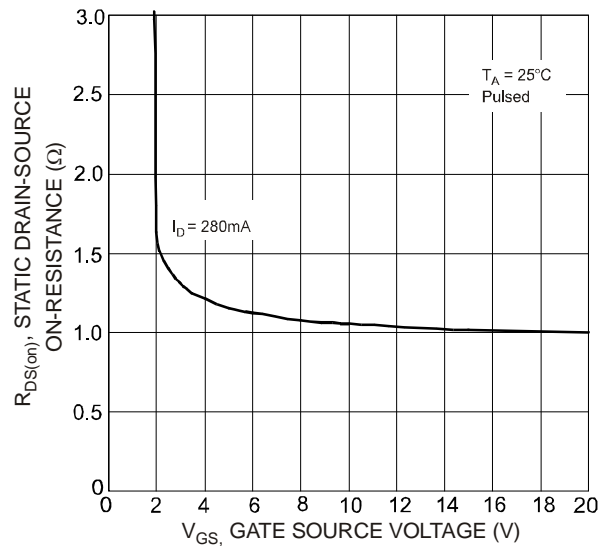


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

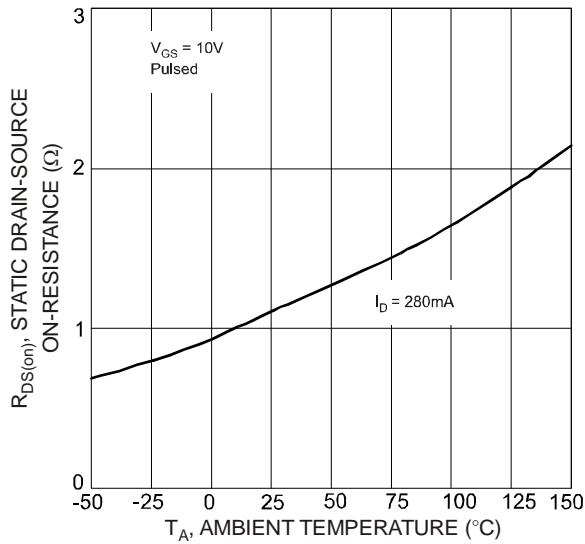


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

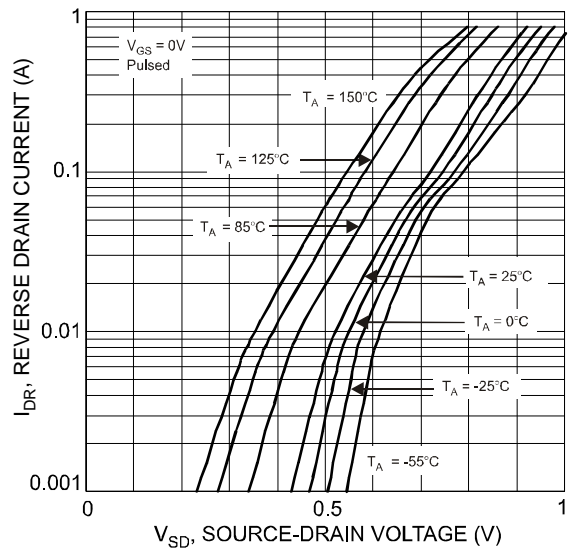


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

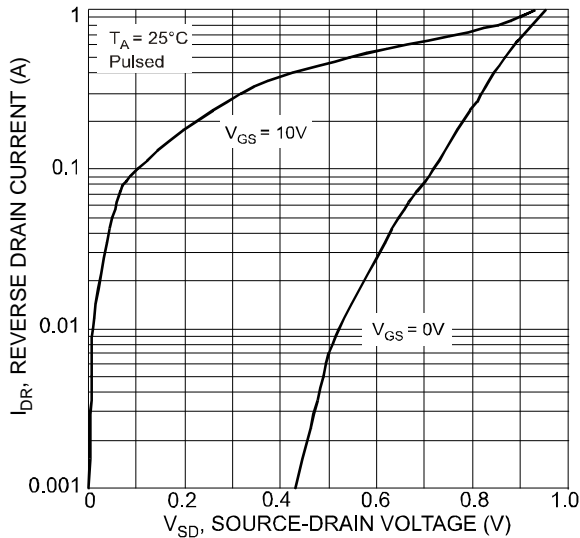


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

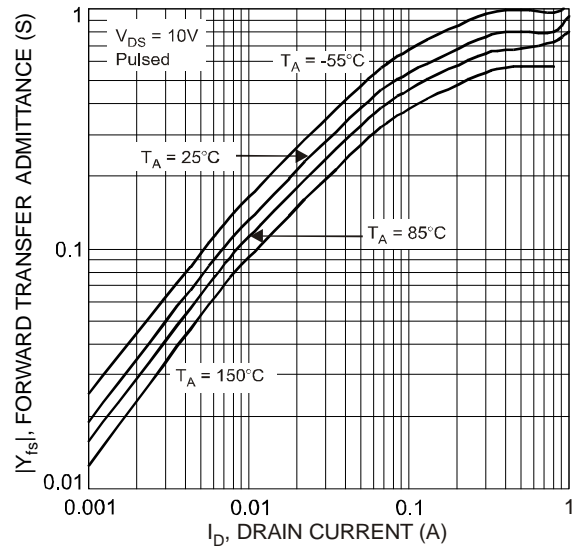
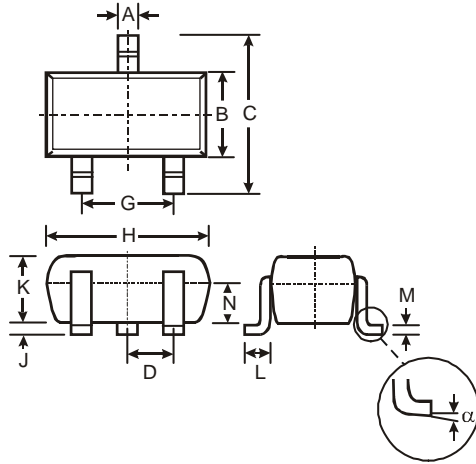


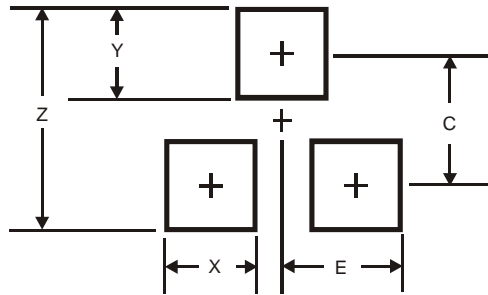
Fig. 10 Forward Transfer Admittance vs. Drain Current

**Package Outline Dimensions**



SOT523			
Dim	Min	Max	Typ
A	0.15	0.30	0.22
B	0.75	0.85	0.80
C	1.45	1.75	1.60
D	—	—	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
J	0.00	0.10	0.05
K	0.60	0.80	0.75
L	0.10	0.30	0.22
M	0.10	0.20	0.12
N	0.45	0.65	0.50
α	0°	8°	—
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	1.8
X	0.4
Y	0.51
C	1.3
E	0.7

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- Техническая поддержка проекта;
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